ITO, $SnO_2$ (Nesa film) and ZnO-Al or, alternatively, base metals such as Ni and Cu provided that the firing of the dielectric layer must be carried out at a partial pressure of oxygen at which these base metals are not oxidized. The lower electrode layer may be formed by known techniques such as sputtering, evaporation, and plating processes.

Al cancel.

## REMARKS

The specification has been amended as supported at page 10, line 22 of the specification as originally filed.

No new matter has been added. Entry and favorable reconsideration are respectfully requested.

Applicants submit that the application is now in condition for examination on the merits. Early notice of such action is earnestly solicited.

Respectfully submitted,

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Serial No.: **09/866,732**
Amendment Filed On: **09/27/01**

**IN THE SPECIFICATION**

Please amend the specification as follows:

Page 10, line 18 and 25, please replace the paragraph with the following paragraph:

--The lower electrode layer should preferably be formed of a material which ensures high electrical conductivity, receives no damage during dielectric layer formation, and has a low reactivity with respect to the dielectric layer or light-emitting layer. Desired for such a lower electrode layer material are noble metals such as Au, Pt, Pd, Ir and Ag, noble metal alloys such as Au-Pd, Au-Pt, Ag-Pd, and Ag-Pt, and electrode materials composed mainly of noble metals such as Ag-Pd-Cu with nonmetal [base metal] elements added thereto, because oxidation resistance with respect to an oxidizing atmosphere used for the firing of the dielectric layer material can be easily obtained. Use may also be made of oxide conductive materials such as ITO, $SnO_2$ (Nesa film) and ZnO-Al or, alternatively, base metals such as Ni and Cu provided that the firing of the dielectric layer must be carried out at a partial pressure of oxygen at which these nonmetals [base metals] are not oxidized. The lower electrode layer may be formed by known techniques such as sputtering, evaporation, and plating processes.--